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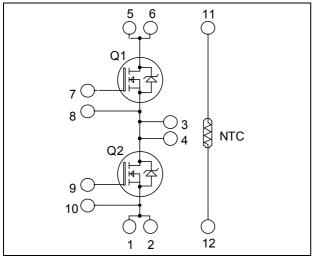
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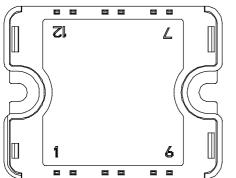
Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





Phase leg Super Junction MOSFET **Power Module**





Absolute maximum ratings

Pulsed Drain current

Gate - Source Voltage

Drain - Source ON Resistance

Maximum Power Dissipation

Repetitive Avalanche Energy

APT0502 on www.microsemi.com

Single Pulse Avalanche Energy

Avalanche current (repetitive and non repetitive)

I_{DM}

V_{GS}

R_{DSon}

 P_D

I_{AR}

 E_{AR}

EAS

Р Symbol Max ratings Unit Parameter Drain - Source Breakdown Voltage 600 V V_{DSS} $T_c = 25^{\circ}C$ 49 I_D Continuous Drain Current $T_c = 80^{\circ}C$ 38 А

	 Low junction to case thermal resistance Solderable terminals both for power at easy PCB mounting Low profile RoHS Compliant
Pins $1/2$; $3/4$; $5/6$ must be shorted together	

APTC60AM45T1G

 $V_{DSS} = 600V$ $R_{DSon} = 45m\Omega \max @ Tj = 25^{\circ}C$ $I_D = 49A$ @ $Tc = 25^{\circ}C$

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
 - Very rugged
- Very low stray inductance Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

 $T_c = 25^{\circ}C$

Benefits

- Outstanding performance at high frequency operation •
- Direct mounting to heatsink (isolated package)
- Low junction to asso thermal resistor
- and signal for

130

 ± 20

45

250

15

3

1900

V

mΩ

W

A

mJ

1 - 7

www.microsemi.com

🗱 CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 600V$ $T_j = 25^{\circ}C$			250	μA
		$V_{GS} = 0V, V_{DS} = 600V$ $T_j = 125^{\circ}C$			500	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 24.5A$		40	45	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 3mA$	2.1	3	3.9	V
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20 V, V_{DS} = 0V$			100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V$; $V_{DS} = 25V$		7.2		nF
C _{oss}	Output Capacitance	f = 1 MHz		8.5		m
Qg	Total gate Charge	$V_{GS} = 10V$		150		
Q_{gs}	Gate – Source Charge	$V_{Bus} = 300V$		34		nC
Q_{gd}	Gate – Drain Charge	$I_D = 49A$		51		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C)		21		
Tr	Rise Time	$V_{GS} = 10V$		30		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 400V$ $I_D = 49A$ $R_G = 5\Omega$		100		ns
$T_{\rm f}$	Fall Time			45		
Eon	Turn-on Switching Energy	Inductive switching @ $25^{\circ}C$ $V_{GS} = 10V$; $V_{Bus} = 400V$		675		I
E _{off}	Turn-off Switching Energy	$V_{GS} = 10V$; $V_{Bus} = 400V$ $I_D = 49A$; $R_G = 5\Omega$		520		μJ
Eon	Turn-on Switching Energy	Inductive switching (a) $125^{\circ}C$		1100		T
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$V_{GS} = 10V$; $V_{Bus} = 400V$ $I_D = 49A$; $R_G = 5Ω$		635		μJ

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Is	Continuous Source current		$Tc = 25^{\circ}C$		49		А
	(Body diode)		$Tc = 80^{\circ}C$		38		A
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -49A$				1.2	V
dv/dt	Peak Diode Recovery 1					4	V/ns
t _{rr}	Reverse Recovery Time	$I_s = -49A$	$T_j = 25^{\circ}C$		600		ns
Q _{rr}	Reverse Recovery Charge	$V_R = 350V$ $di_s/dt = 100A/\mu s$	$T_j = 25^{\circ}C$		17		μC

• dv/dt numbers reflect the limitations of the circuit rather than the device itself. $I_S \leq -49A$ di/dt $\leq 100A/\mu s$ $V_R \leq V_{DSS}$ $T_j \leq 150^{\circ}C$



Thermal and package characteristics

Symbol	Characteristic		Min	Тур	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance					0.5	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		4000			V	
TJ	Operating junction temperature range		-40		150		
T _{STG}	Storage Temperature Range		-40		125	°C	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					80	g

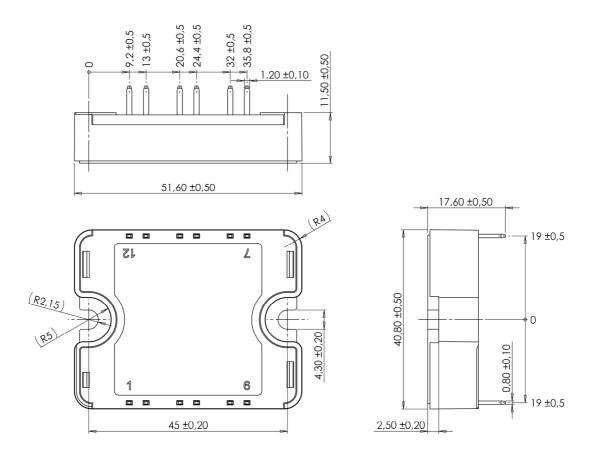
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$= \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP1 Package outline (dimensions in mm)

 R_T



See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

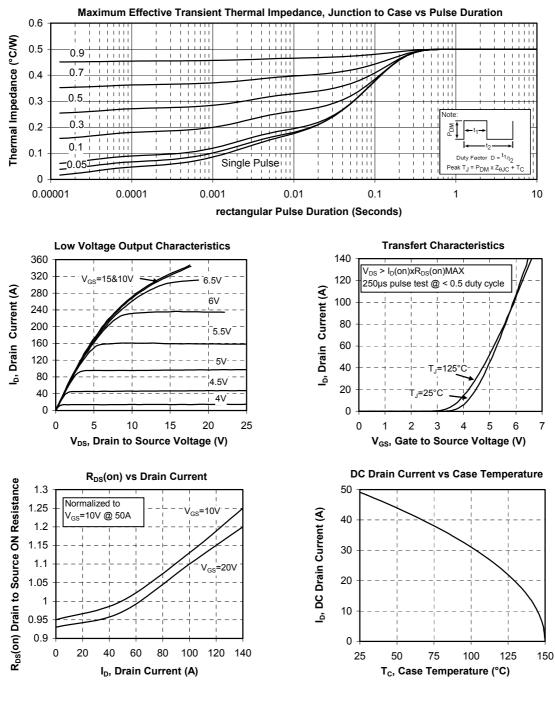
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3 - 7



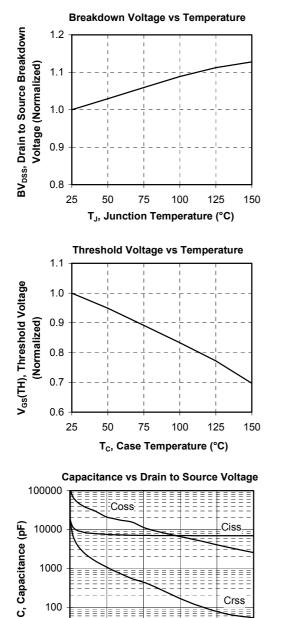
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Typical Performance Curve



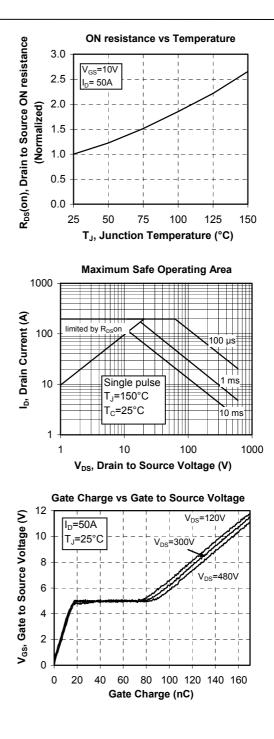
APTC60AM45T1G-Rev 1 October, 2012





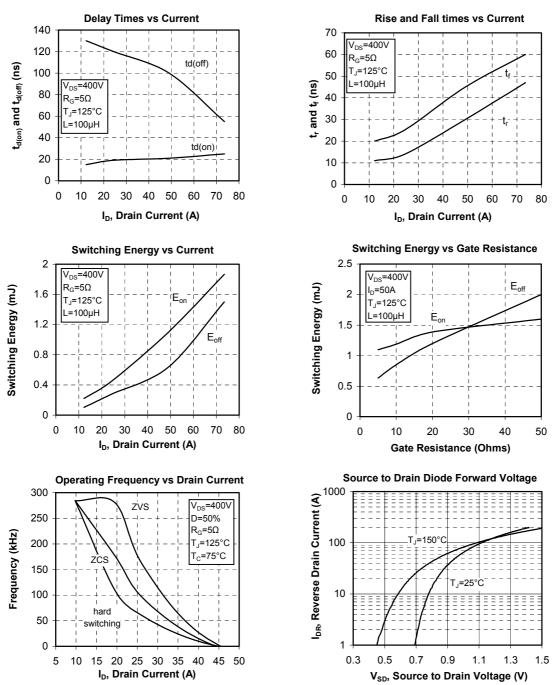
V_{DS}, Drain to Source Voltage (V)

APTC60AM45T1G





APTC60AM45T1G



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APTC60AM45T1G

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